MICRO ELECTRONICS

MI33T
MIB33T

INFRARED EMITTING DIODE

DESCRIPTION

MI33T & MIB33T are GaAs infrared emitting diode molded in a flangeless 3mm diameter clear plastic package, with the lensing effect of the package, and MIB33T with cup type leadframe.
MI33T & MIB33T are mechanically and spectrally matched to the MEL81N series photo transistor.

ABSOLUTE MAXIMUM RATINGS

Forward Current (Continuous)	100mA
Pulse Forward Current	1A*
Reverse Voltage (Continuous)	5V
Power Dissipation	100mW
Operating Temperature Range	-20 to +90°C
Lead Soldering Temperature (1/16" from body)	260°C for 5 sec.

* Pulse Width = 10μs, Duty Ratio = 0.01.

ELECTRO-OPTICAL CHARACTERISTICS (Ta=25°C)

PARAMETER		SYMBOL	MI33T	MIB33T	UNIT	CONDITIONS
Radiant Power Output	MIN	Po	2.0	2.5	mW	IF=20mA
	TYP	Po	4.0	4.5	mW	IF=20mA
Forward Voltage	MAX	VF	1.6	1.6	V	IF=20mA
Reverse Current	MAX	IR	10	10	μA	VR=5V
Half Intensity Beam Angle	TYP	θHI	30	18	degree	IF=20mA
Peak Wavelength	TYP	$\lambda\rho$	940	940	nm	IF=20mA
Spectrum Line Half Width	TYP	$\Delta\lambda$	45	45	nm	IF=20mA

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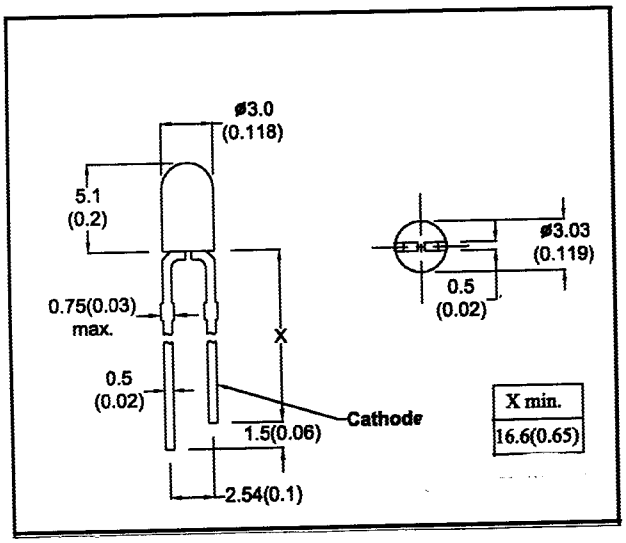
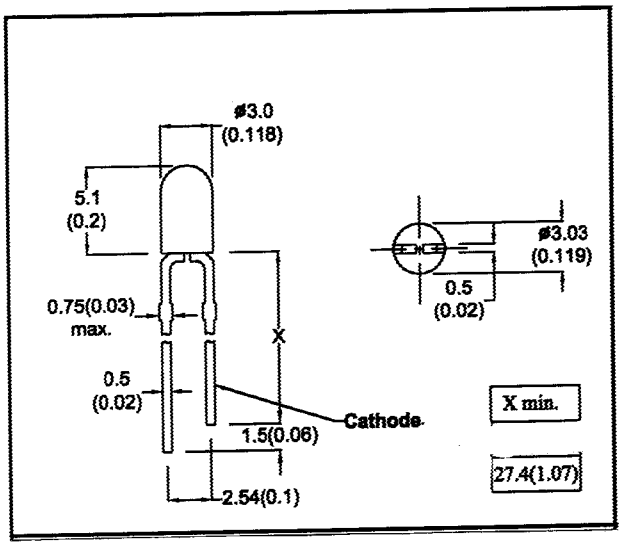
MI33T



- All dimension in mm(inch)
- No Scale
- Tol. : +/-0.3mm

MIB33T



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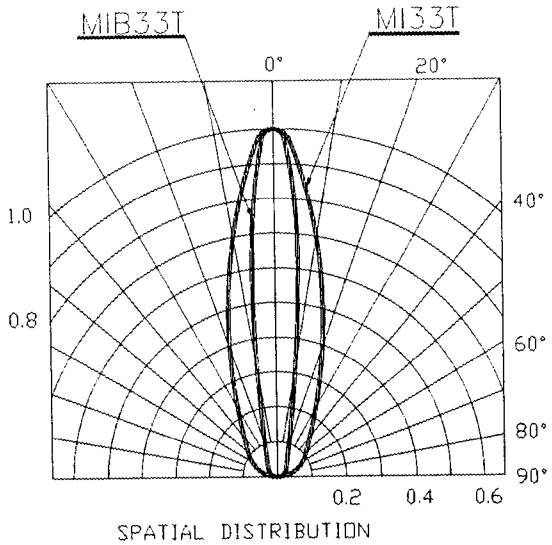
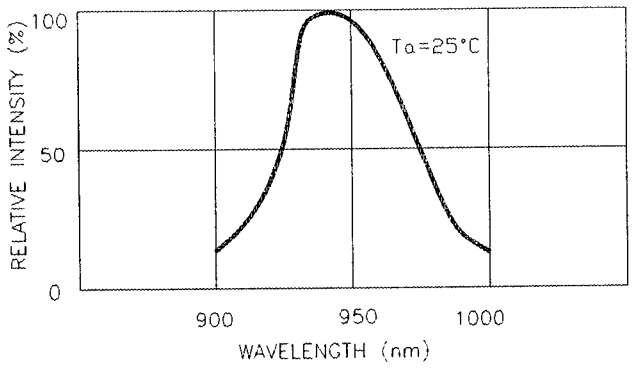
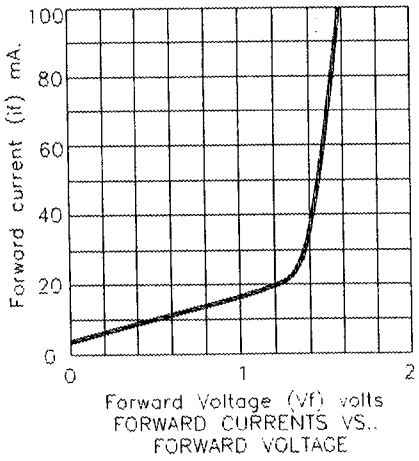


SPATIAL DISTRIBUTION

MI33T,MIB33T

RELATIVE INTENSITY VS.WAVELENGTH





FORWARD CURRENTS VS..
FORWARD VOLTAGE

POWER DISSIPATION